

**ABSTRACT**

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**Fault Tolerant Magnetoresistive  
Solid-state Storage Device**

10 A magnetoresistive solid-state storage device (MRAM)  
performs error correction coding (ECC) of stored  
information. At manufacture or during use, each logical  
block of ECC encoded data and/or the corresponding set of  
storage cells are evaluated to determine suitability for  
continued use, or whether remedial action is necessary.  
15 In a first preferred method ECC decoding is attempted to  
determine whether information is unrecoverable from the  
block of ECC encoded data. In a second preferred method a  
parametric evaluation is made prior to attempting ECC  
decoding.

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[Figure 3]

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